



**Supplementary Materials** 

# A Windmill-Shaped Molecule with Anthryl Blades to Form Smooth Hole-Transport Layers via a Photoprecursor Approach

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#### 1. Computation

The structure of TAT was optimized at the B3LYP/6-31G(d) level of theory with a C<sub>3</sub>-symmetry constraint. The estimated HOMO and LUMO energies are -5.14 and -1.93 eV; thus, the HOMO of TAT is somewhat stabilized as compared to those of the previously employed p-sublayer materials DTA and PhBADT (Figure S1a). In terms of the HOMO–LUMO energy difference, TAT ( $\Delta E_{HOMO-LUMO}$  = 3.21 eV) was calculated to be in between DTA (3.18 eV) and PhBADT (3.29 eV). The optimized conformation is rather planar with dihedral angles below 30° (Figure S1b, Table S1), which is favorable for forming  $\pi$ – $\pi$  stacking in the thin-film state.



**Figure S1.** Results of the DFT computation on TAT performed at the B3LYP/6-31G(d) level of theory: (a) Frontier orbital energies in comparison with those of DTA and PhBADT; (b) Top and side views of the optimized structure. The relevant dihedral angles are shown in the top view.

Atom No.	Symbol	X	Y	Ζ	Atom No.	Symbol	X	Y	Z
1	С	1.193	0.723	0.960	51	С	4.725	-5.430	0.121
2	С	-0.029	1.411	0.964	52	С	5.539	-6.557	-0.193
3	С	-1.222	0.671	0.960	53	С	6.973	-6.392	-0.233
4	С	-1.208	-0.731	0.964	54	С	7.508	-5.094	0.038
5	С	0.030	-1.394	0.960	55	С	6.694	-4.035	0.325
6	С	1.237	-0.681	0.964	56	С	4.993	-7.820	-0.458

Table S1. Atomic coordinates of the optimized structure of TAT.

Materials 2020, 13, x FOR PEER REVIEW

2	of	12
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7	С	2.533	-1.371	0.975	57	С	5.801	-8.924	-0.762
8	С	-0.079	2.878	0.975	58	С	7.236	-8.756	-0.801
9	С	-2.453	-1.508	0.975	59	С	7.781	-7.492	-0.535
10	С	-1.054	3.697	1.501	60	С	5.255	-10.217	-1.036
11	С	-0.786	5.081	1.344	61	С	6.071	-11.278	-1.330
12	С	0.402	5.350	0.697	62	С	7.486	-11.112	-1.369
13	S	1.191	3.847	0.255	63	С	8.049	-9.889	-1.112
14	С	-2.674	-2.762	1.501	64	Н	2.123	1.283	0.952
15	С	-4.007	-3.221	1.344	65	Н	-2.172	1.197	0.952
16	С	-4.834	-2.327	0.697	66	Η	0.050	-2.479	0.952
17	S	-3.927	-0.892	0.255	67	Η	-1.926	3.314	2.021
18	С	3.729	-0.935	1.501	68	Н	-1.435	5.857	1.733
19	С	4.793	-1.860	1.344	69	Н	-1.907	-3.325	2.021
20	С	4.432	-3.023	0.697	70	Η	-4.355	-4.172	1.733
21	S	2.736	-2.955	0.255	71	Н	3.833	0.011	2.021
22	С	5.264	-4.185	0.377	72	Η	5.790	-1.685	1.733
23	С	-6.256	-2.466	0.377	73	Η	3.008	5.950	0.173
24	С	0.992	6.651	0.377	74	Η	0.000	9.914	-0.002
25	С	2.340	6.807	0.121	75	Η	-0.918	7.699	0.496
26	С	2.909	8.075	-0.193	76	Η	4.926	7.362	-0.428
27	С	2.049	9.235	-0.233	77	Η	1.947	11.356	-0.565
28	С	0.657	9.049	0.038	78	Η	6.868	8.786	-1.006
29	С	0.148	7.815	0.325	79	Η	7.792	11.013	-1.537
30	С	4.276	8.234	-0.458	80	Η	3.888	12.786	-1.141
31	С	4.828	9.486	-0.762	81	Η	-6.656	-0.370	0.173
32	С	3.965	10.644	-0.801	82	Η	-8.586	-4.957	-0.002
33	С	2.598	10.485	-0.535	83	Н	-6.209	-4.644	0.496
34	С	6.220	9.660	-1.036	84	Η	-8.839	0.585	-0.428
35	С	6.731	10.896	-1.330	85	Н	-10.808	-3.992	-0.565
36	С	5.880	12.039	-1.369	86	Н	-11.043	1.554	-1.006
37	С	4.540	11.915	-1.112	87	Н	-13.434	1.241	-1.537
38	С	-7.065	-1.377	0.121	88	Η	-13.017	-3.026	-1.141
39	С	-8.448	-1.518	-0.193	89	Н	3.649	-5.579	0.173
40	С	-9.022	-2.843	-0.233	90	Н	8.586	-4.957	-0.002
41	С	-8.165	-3.955	0.038	91	Н	7.127	-3.055	0.496
42	С	-6.842	-3.780	0.325	92	Η	3.913	-7.947	-0.428
43	С	-9.269	-0.414	-0.458	93	Н	8.861	-7.364	-0.565
44	С	-10.629	-0.562	-0.762	94	Н	4.175	-10.341	-1.006
45	С	-11.201	-1.888	-0.801	95	Η	5.642	-12.254	-1.537
46	С	-10.379	-2.992	-0.535	96	Η	9.129	-9.760	-1.141
47	С	-11.475	0.557	-1.036	97	Η	8.117	-11.965	-1.604
48	С	-12.802	0.381	-1.330	98	Η	6.303	13.012	-1.604
49	С	-13.366	-0.927	-1.369	99	Н	-14.420	-1.047	-1.604
50	C	-12 589	-2 026	-1 112	_	_	_	_	_

2. NMR spectra of the photoprecursor TAT(DK)<sub>2</sub>



Figure S3. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 2 (CDCl<sub>3</sub>, 101 MHz).



Figure S5. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 3 (CDCl<sub>3</sub>, 101 MHz).



Figure S7. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 4 (CDCl<sub>3</sub>, 101 MHz).





Figure S9. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 5 (CDCl<sub>3</sub>, 101 MHz).



Figure S11. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 6 (CDCl<sub>3</sub>, 101 MHz).



Figure S13. <sup>13</sup>C{<sup>1</sup>H} NMR spectrum of compound 8 (CDCl<sub>3</sub>, 101 MHz).







Figure S16. <sup>13</sup>C{<sup>1</sup>H} NMR spectra of TAT(DK)<sub>2</sub> (CDCl<sub>3</sub>, 101 MHz).

#### 3. Additional Atomic-Force-Microscopy Images



**Figure S17.** Tapping-mode AFM images of thin films prepared through the photoprecursor approach: (a) TAT ( $R_{RMS} = 1.0 \text{ nm}$ ); (b) PhBADT (12.4 nm). The scale bars correspond to 1.0 µm. See references 16 and 21 for additional AFM images of DTA.

## 4. Hole Mobility in EBDBTA

The hole mobility in EBDBTA was estimated by the SCLC method in a hole-only device with a structure of [ITO/MoO<sub>3</sub> (10 nm)/EBDBTA (75 nm)/MoO<sub>3</sub> (10 nm)/Al (80 mn)]. The EBDBTA was deposited through the photoprecursor approach as described in a previous paper [1]. The hole mobility was estimated as  $6.4 \times 10^{-5}$  cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>.



**Figure S18.** *J*–*V* curve of the hole-only device with EBDBTA. Voltage for the observed data is defined as  $V_{appl}-V_{bi}-V_{s}$ , wherein  $V_{appl}$  is the applied voltage,  $V_{bi}$  is the estimated built-in voltage, and  $V_{s}$  is the estimated voltage drop associated with series resistance.

#### 5. Photoelectron Spectroscopy of TAT

The ionization energy of EBDBTA was determined as 5.6 eV by photoelectron spectroscopy in air as described in Section 4 of the main text.



Figure S19. Photoelectron spectrum of TAT deposited via the photoprecursor approach on ITO substrate.

## 6. Semi-Log Current-Density-Voltage Plots of the p-i-n Devices



**Figure S20.** Semi-log *J*–*V* plots for the p–i–n-type OPVs comprising different p-sublayer materials: (a) TAT; (b) DTA; (c) PhBADT. The data are the same as those plotted in Figure 8 in the main text.

## Reference

 Suzuki, M.; Terai, K.; Quinton, C.; Hayashi, H.; Aratani, N.; Yamada, H. Open-circuit-voltage shift of over 0.5 V in organic photovoltaic cells induced by a minor structural difference in alkyl substituents. *Chem. Sci.* 2020, *11*, 1825–1831.



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